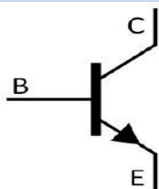


Silicon NPN transistor in a SOT-23 Plastic Package.

Low current, Low voltage.

General power amplifier and switching application.

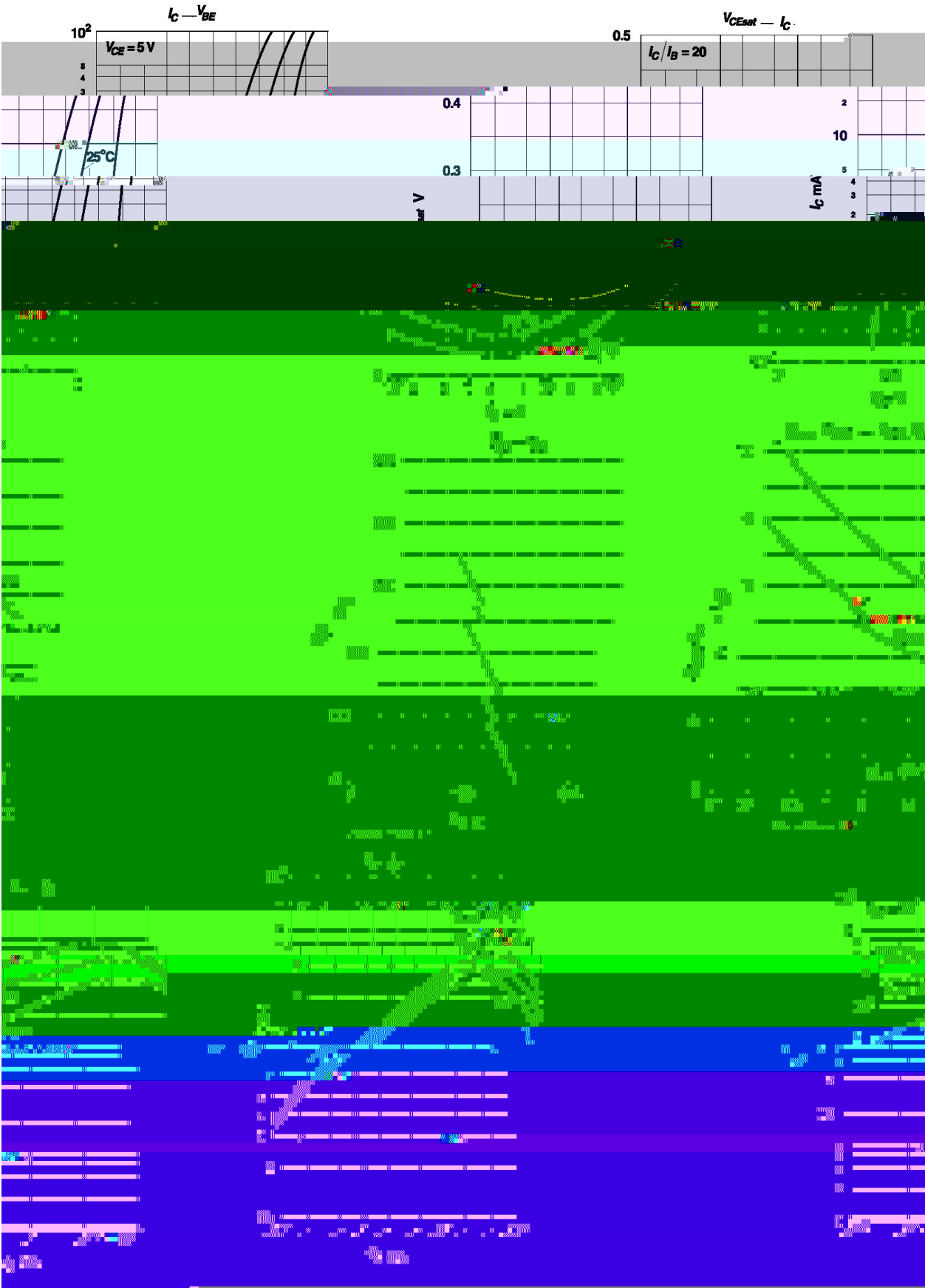


PIN1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	A	B
h_{FE} Range	110 220	200 450
Marking	1AH	H1B

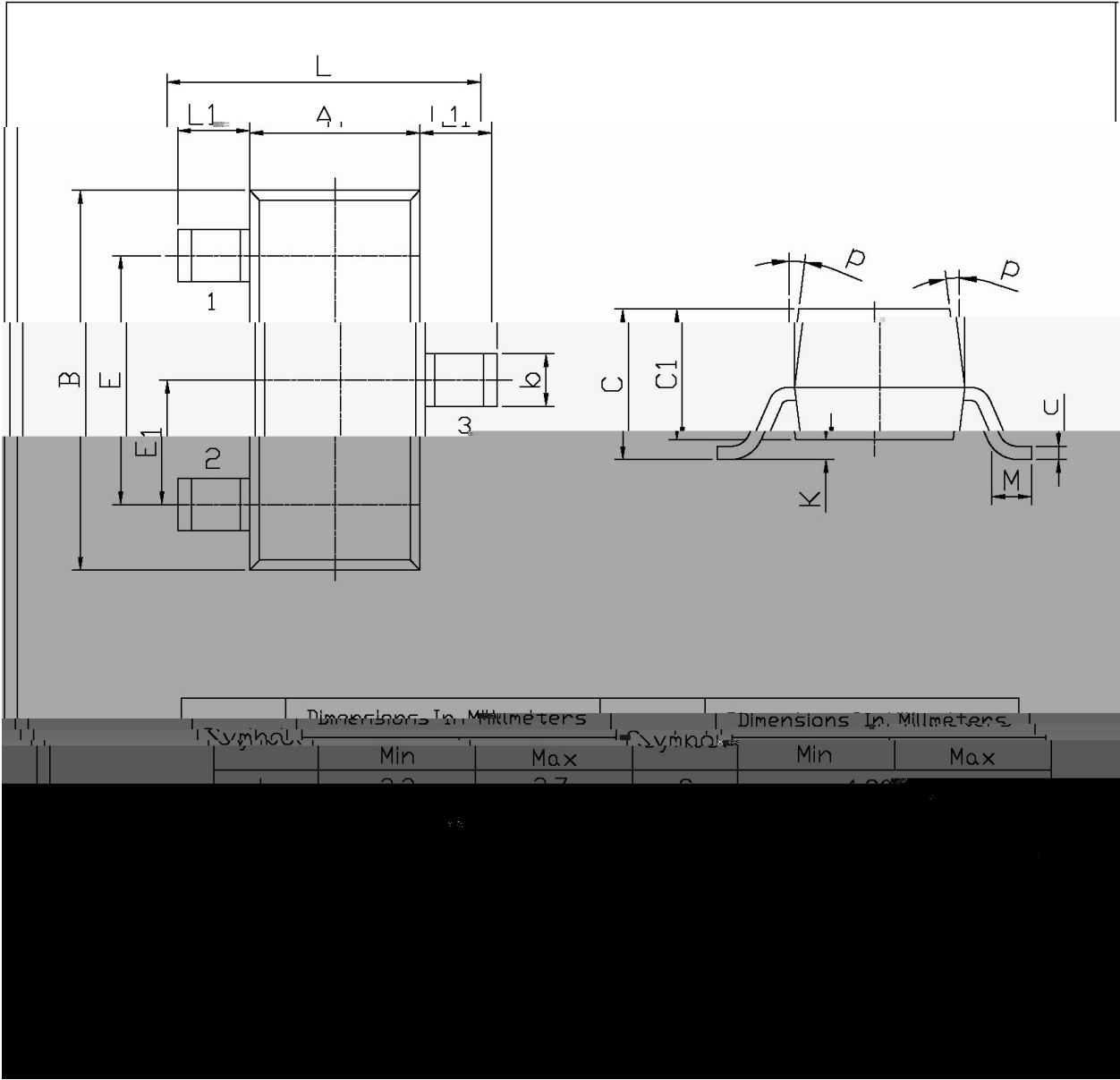
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	65	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

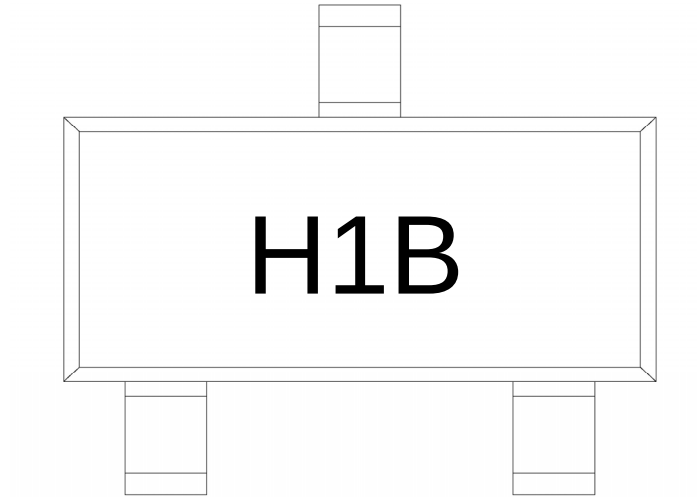
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.015	A
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=2.0mA$	110		450	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=10mA$ $I_B=0.5mA$		0.09	0.25	V
	$V_{CE(sat)(2)}$	$I_C=100mA$ $I_B=5.0mA$		0.2	0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=10mA$ $I_B=0.5mA$		0.7		V
	$V_{BE(sat)(2)}$	$I_C=100mA$ $I_B=5.0mA$		0.9		V
Base to Emitter Voltage	$V_{BE(1)}$	$V_{CE}=5.0V$ $I_C=2.0mA$	0.58		0.7	V
	$V_{BE(2)}$	$V_{CE}=5.0V$ $I_C=10mA$			0.75	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $f=100MHz$ $I_C=10mA$		300		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		2.5	4.5	pF



SOT-23

单位; mm

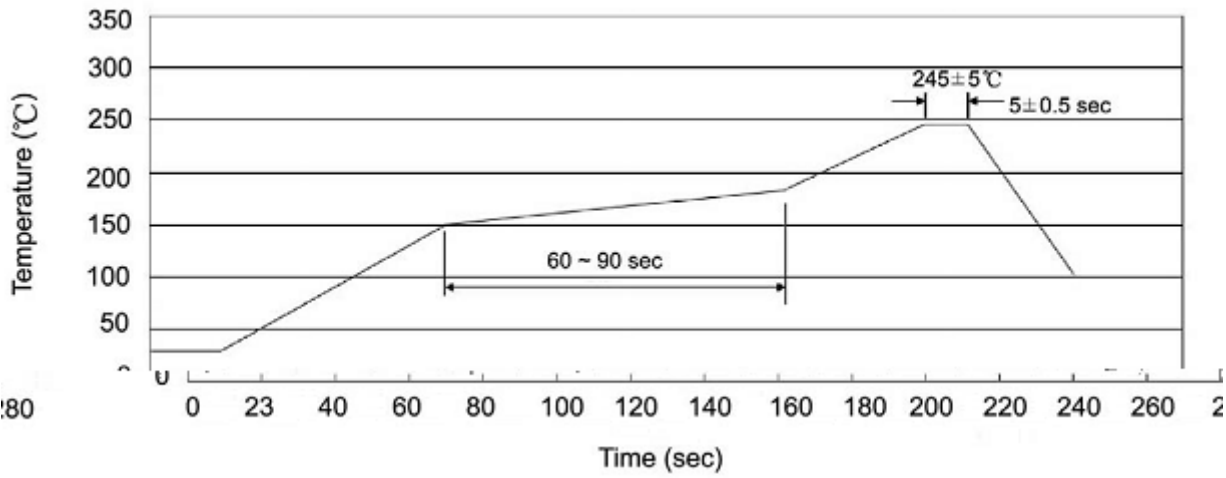




Note:

H: Company Code.

1B: Product Type Code



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱